Assembly Process Data Sheet Wafer Bump Assembly Materials Part number change Wafer Bump Mechanical Specification Test Site Wafer Fab S Packing/Shipping/Labeling Test Process Wafer Fab S Vafer Fab F Wafer Fab F Percent Packing/Shipping/Labeling Test Process Wafer Fab F Wafer Fab F Wafer Fab F Percent Packing Wafer Fab F Packing Wafer Fab F Pac	t Sample p Site p Material p Process Site Materials Process as Additional	s Provided at S est Wafer Bump Wafer Bump Wafer Bump Wafer Fab Si Wafer Fab Ma Wafer Fab Pr	rvic Date	Quality Se Sample [y: r	pt: Estimate Availabili sign ta Sheet t number o	Dep 2017	N Manager	evices	Package De r Contact: I 1 st Ship Da Type: mbly Site	Customer Proposed Change T
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Mechanical Specification ☑ Test Site ☑ Wafer Fab S ☑ Packing/Shipping/Labeling ☑ Test Process ☑ Wafer Fab N ☑ Wafer Fab F PCN Details ☑ Wafer Fab F Description of Change: PCN Details ☑ Wafer Fab F Description of Change: PCN Details ☑ Wafer Fab F Texas Instruments Incorporated is announcing the qualification of HANA Thailand as Assembly and Test Site for select devices listed in the "Product Affected" Section. Coassembly sites and Material differences are as follows. Assembly Site Assembly Site Origin Assembly Country Code Assembly S Hitachi HTC JPN Kitatsugaru, HANA Thailand HNT THA Ayutthe Material Differences: Hitachi HANA Thailand Mount Compound RZ241C F400728 F400728 	Site Materials Process as Additional	Wafer Fab Si Wafer Fab Ma Wafer Fab Pr		nange						
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Mount Compound RZ241C F400728	Material Differences:									
									Compound	Mount (
Wold compound Goodk P450524										
Test coverage, insertions, conditions will remain consistent with current testing and test MQ. Reason for Change: Continuity of supply. Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / I None Changes to product identification resulting from this PCN:										
changes to product identification resulting from this PCN.						resulti	incation	uem	to product	changes
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Assembly Site Hitachi Assembly Site Origin (22L) ASO: HT	тс	ASO: HTC		(221)	ly Site Origi	Assamble			y Site	
		ASO: HNT							ailand	

Product Affected:			
74AVCH2T45DCTRE4	SN74AUC2G79DCTR	SN74LVC2G08DCTR	SN74LVC3G04DCTRG4
74AVCH2T45DCTTE4	SN74AUC2G80DCTR	SN74LVC2G08DCTRE4	SN74LVC3G06DCTR
74LVC1G123DCTRE4	SN74AUC2G80DCTRG4	SN74LVC2G08DCTRG4	SN74LVC3G06DCTRE4
74LVC1G123DCTRG4	SN74AUC2G86DCTR	SN74LVC2G125DCTR	SN74LVC3G07DCTR
74LVC1G123DCTTE4	SN74AUP1G99DCTR	SN74LVC2G132DCTR	SN74LVC3G07DCTRG4
74LVC1G123DCTTG4	SN74AUP1G99DCTT	SN74LVC2G157DCTR	SN74LVC3G14DCTR
74LVC1G139DCTRE4	SN74AVC2T45DCTR	SN74LVC2G157DCTR-P	SN74LVC3G14DCTR-P
74LVC1G139DCTTE4	SN74AVC2T45DCTRE4	SN74LVC2G157DCTRG4	SN74LVC3G14DCTRE4
74LVC2G125DCTR-P2	SN74AVC2T45DCTT	SN74LVC2G240DCTR	SN74LVC3G14DCTRG4
74LVC2G125DCTRE4	SN74AVC2T45DCTTG4	SN74LVC2G32DCTR	SN74LVC3G17DCTR
74LVC2G125DCTRG4	SN74AVCH2T45DCTR	SN74LVC2G32DCTRE4	SN74LVC3G17DCTRE4
74LVC2G132DCTRG4	SN74AVCH2T45DCTT	SN74LVC2G32DCTRG4	SN74LVC3G17DCTRG4
74LVC2G157DCTRE4	SN74LVC1404DCTR	SN74LVC2G38DCTR	SN74LVC3G34DCTR
74LVC2G240DCTRE4	SN74LVC1G123DCTR	SN74LVC2G66DCTR	SN74LVC3G34DCTR-P
LSF0102DCTR	SN74LVC1G123DCTT	SN74LVC2G66DCTRE4	SN74LVC3G34DCTRG4
SN74AUC2G00DCTR	SN74LVC1G139DCTR	SN74LVC2G66DCTRG4	SN74LVC3GU04DCTR
SN74AUC2G00DCTRE4	SN74LVC1G139DCTT	SN74LVC2G79DCTR	SN74TVC3306DCTR
SN74AUC2G02DCTR	SN74LVC1G29DCTR	SN74LVC2G80DCTR	SN74TVC3306DCTRE4
SN74AUC2G08DCTR	SN74LVC1G99DCTR	SN74LVC2G80DCTRG4	TCA9406DCTR
SN74AUC2G08DCTRE4	SN74LVC1G99DCTRG4	SN74LVC2G86DCTR	TS5A2053DCTR
SN74AUC2G08DCTRG4	SN74LVC1G99DCTT	SN74LVC2G86DCTRG4	TS5A2053DCTRE4
SN74AUC2G125DCTR	SN74LVC2G00DCTR	SN74LVC2T45DCTR	TXS0102DCTR
SN74AUC2G126DCTR	SN74LVC2G00DCTRE4	SN74LVC2T45DCTRE4	TXS0102DCTRE4
SN74AUC2G240DCTR	SN74LVC2G00DCTRG4	SN74LVC2T45DCTT	TXS0102DCTT
SN74AUC2G241DCTR	SN74LVC2G02DCTR	SN74LVC2T45DCTTG4	TXS0102DCTTE4
SN74AUC2G32DCTR	SN74LVC2G02DCTRE4	SN74LVC3G04DCTR	TXS0102DCTTG4
SN74AUC2G66DCTR	SN74LVC2G02DCTRG4	SN74LVC3G04DCTRE4	

Qualification Report

New Package: DCT package qual at HNT

Approve Date 18-Oct-2016

Product Attributes

Attributes	Qual Device: PCA9306DCTR	Qual Device: TXS0102DCTR
Assembly Site	HNT	HNT
Package Family	SSOP	SSOP
Flammability Rating	UL 94 V-0	UL 94 V 0
Wafer Fab Supplier	SFAB	FFAB
Wafer Process	EPIC1ZS	A3C10TPI /P9785

- QBS: Qual By Similarity

- Qual Devices qualified at LEVEL1-260C:PCA9306DCTR, TXS0102DCTR

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: PCA9306DCTR	Qual Device: TXS0102DCTR
AC	Autoclave 121C	96 Hours	3/231/0	3/231/0
FLAM	Flammability (IEC 695-2-2)		-	3/15/0
FLAM	Flammability (UL 94V-0)		-	3/15/0
FLAM	Flammability (UL-1694)		-	3/15/0
HAST	Biased HAST, 130C/85%RH	96 Hours	-	3/231/0
HTOL	Life Test, 150C	300 Hours	-	3/231/0
HTSL	High Temp Storage Bake 170C	420 Hours	3/231/0	3/231/0
LI	Lead Fatigue	Leads	-	3/66/0
LI	Lead Pull to Destruction	Leads	-	3/66/0
PD	Physical Dimensions		-	3/15/0
SD	Surface Mount Solderability	Pb Free	-	3/66/0
SD	Surface Mount Solderability	Pb	-	3/66/0
TC	Temperature Cycle, -65/150C	500 Cycles	3/231/0	3/231/0
WBP	Bond Pull	Wires	3/228/0	3/228/0
WBS	Ball Bond Shear	Wires	3/228/0	3/228/0

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours,

150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

Qualification Report

A-T / Device Offload into HNT DCT package

Approve Date 19-Oct-2016

Product Attributes

Attributes	Qual Device: SN74LVC2G66DCTR	QBS Package Reference: TXS0102DCTR	
Assembly Site	HNT	HNT	
Package Family	SSOP	SSOP	
Flammability Rating	UL 94 V-0	UL 94 V 0	
Wafer Fab Supplier	FFAB	FFAB	
Wafer Process	A3CTPI-8	A3C10TPI	

- QBS: Qual By Similarity

- Qual Device SN74LVC2G66DCTR is qualified at LEVEL1-260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: SN74LVC2G66DCTR	QBS Package Reference: TXS0102DCTR
AC	Autoclave 121C	96 Hours	3/231/0	3/231/0
FLAM	Flammability (IEC 695-2-2)		-	3/15/0
FLAM	Flammability (UL 94V-0)		-	3/15/0
FLAM	Flammability (UL-1694)		-	3/15/0
HAST	Biased HAST, 130C/85%RH	96 Hours	-	3/231/0
HTOL	Life Test, 150C	300 Hours	-	3/231/0
HTSL	High Temp. Storage Bake, 170C	420 Hours	3/231/0	3/231/0
LI	Lead Fatigue	Leads	-	3/66/0
LI	Lead Pull to Destruction	Leads	-	3/66/0
PD	Physical Dimensions		-	3/15/0
SD	Surface Mount Solderability	Pb Free	-	3/66/0
SD	Surface Mount Solderability	Pb	-	3/66/0
TC	Temperature Cycle, -65/150C	500 Cycles	3/231/0	3/231/0
WBP	Bond Pull	Wires	3/228/0	3/228/0
WBS	Ball Bond Shear	Wires	3/228/0	3/228/0

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours,

150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

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Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com